Preferred Device

# **Dual Schottky Barrier Diodes**

Application circuit designs are moving toward the consolidation of device count and into smaller packages. The new SOT-363 package is a solution which simplifies circuit design, reduces device count, and reduces board space by putting two discrete devices in one small six-leaded package. The SOT-363 is ideal for low-power surface mount applications where board space is at a premium, such as portable products.

### **Surface Mount Comparisons:**

	SOT-363	SOT-23
Area (mm <sup>2</sup> )	4.6	7.6
Max Package P <sub>D</sub> (mW)	120	225
Device Count	2	1

### **Space Savings:**

Package	1 × SOT-23	2 × SOT-23		
SOT-363	40%	70%		

The MBD110DW, MBD330DW, and MBD770DW devices are spin-offs of our popular MMBD101LT1, MMBD301LT1, and MMBD701LT1 SOT-23 devices. They are designed for high-efficiency UHF and VHF detector applications. Readily available to many other fast switching RF and digital applications.

### Features

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage
- Pb-Free Packages are Available

### **MAXIMUM RATINGS**

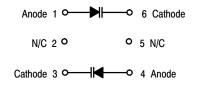
Rating		Symbol	Value	Unit
Reverse Voltage	MBD110DWT1 MBD330DWT1 MBD770DWT1	V <sub>R</sub>	7.0 30 70	Vdc
Forward Power Dissipation T <sub>A</sub> = 25°C		P <sub>F</sub>	120	mW
Junction Temperature		TJ	-55 to +125	°C
Storage Temperature Range		T <sub>stg</sub>	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



### ON Semiconductor®

### http://onsemi.com





SC-88 / SOT-363 CASE 419B STYLE 6

#### MARKING DIAGRAM



xx = Device Code

Refer to Ordering Table,

page 2

M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 10 μA)	MBD110DWT1 MBD330DWT1 MBD770DWT1	V <sub>(BR)R</sub>	7.0 30 70	10 - -	- - -	V
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz, Note 1)	MBD110DWT1	C <sub>T</sub>	_	0.88	1.0	pF
Total Capacitance $(V_R = 15 \text{ Volts}, f = 1.0 \text{ MHz})$ $(V_R = 20 \text{ Volts}, f = 1.0 \text{ MHz})$	MBD330DWT1 MBD770DWT1	C <sub>T</sub>		0.9 0.5	1.5 1.0	pF
Reverse Leakage (V <sub>R</sub> = 3.0 V) (V <sub>R</sub> = 25 V) (V <sub>R</sub> = 35 V)	MBD110DWT1 MBD330DWT1 MBD770DWT1	I <sub>R</sub>		0.02 13 9.0	0.25 200 200	μΑ nAdc nAdc
Noise Figure (f = 1.0 GHz, Note 2)	MBD110DWT1	NF	_	6.0	_	dB
Forward Voltage (I <sub>F</sub> = 10 mA) (I <sub>F</sub> = 1.0 mAdc) (I <sub>F</sub> = 1.0 mA) (I <sub>F</sub> = 1.0 mAdc) (I <sub>F</sub> = 1.0 mAdc)	MBD110DWT1 MBD330DWT1 MBD770DWT1	V <sub>F</sub>	- - - -	0.5 0.38 0.52 0.42 0.7	0.6 0.45 0.6 0.5 1.0	Vdc

### **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
MBD110DWT1		SC-88 / SOT-363	
MBD110DWT1G	M4	SC-88 / SOT-363 (Pb-Free)	
MBD330DWT1		SC-88 / SOT-363	
MBD330DWT1G	T4 SC-88 / SOT-363 (Pb-Free)		3000 Units / Tape & Reel
MBD770DWT1		SC-88 / SOT-363	
MBD770DWT1G	H5	SC-88 / SOT-363 (Pb-Free)	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# TYPICAL CHARACTERISTICS MBD110DWT1

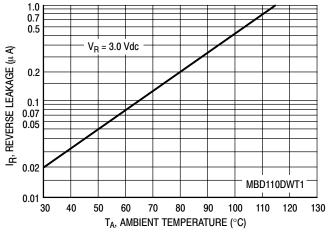


Figure 1. Reverse Leakage

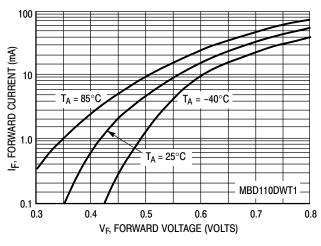


Figure 2. Forward Voltage

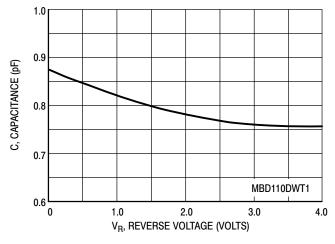


Figure 3. Capacitance

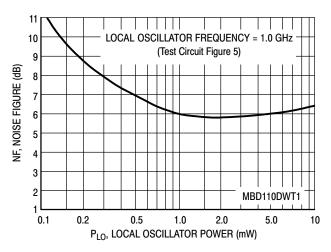


Figure 4. Noise Figure

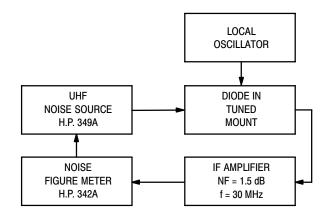
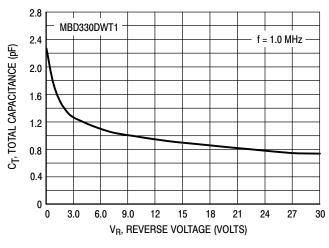


Figure 5. Noise Figure Test Circuit

### NOTES ON TESTING AND SPECIFICATIONS

- Note 1 C<sub>C</sub> and C<sub>T</sub> are measured using a capacitance bridge (Boonton Electronics Model 75A or equivalent)
- Note 2 Noise figure measured with diode under test in tuned diode mount using UHF noise source and local oscillator (LO) frequency of 1.0 GHz. The LO power is adjusted for 1.0 mW. IF amplifier NF = 1.5 dB, f = 30 MHz, see
- Note 3 L<sub>S</sub> is measured on a package having a short instead of a die, using an impedance bridge (Boonton Radio Model 250A RX Meter).

# TYPICAL CHARACTERISTICS MBD330DWT1



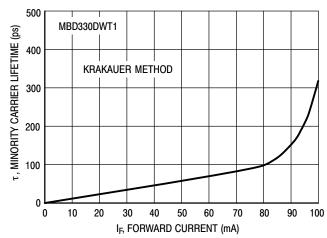
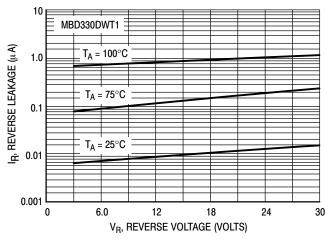


Figure 6. Total Capacitance

Figure 7. Minority Carrier Lifetime



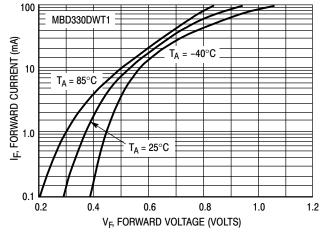
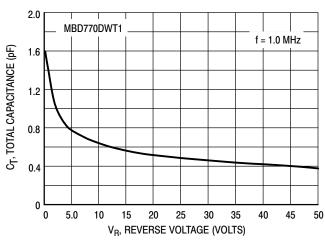


Figure 8. Reverse Leakage

Figure 9. Forward Voltage

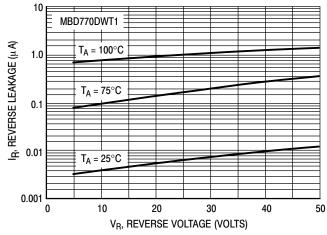
# TYPICAL CHARACTERISTICS MBD770DWT1



(8) MBD770DWT1 WBD770DWT1 WBD770DWT1 100 KRAKAUER METHOD 100 100 20 30 40 50 60 70 80 90 100 I<sub>F</sub>, FORWARD CURRENT (mA)

Figure 10. Total Capacitance

Figure 11. Minority Carrier Lifetime





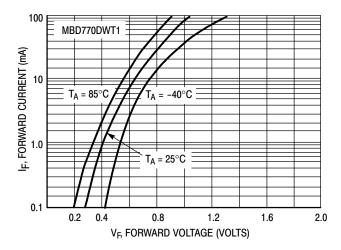
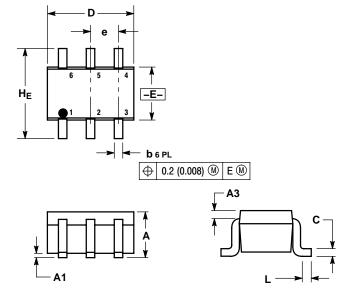


Figure 13. Forward Voltage

### PACKAGE DIMENSIONS

SC-88 / SC-70 / SOT-363 CASE 419B-02 ISSUE W



#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14 5M 1982
- CONTROLLING DIMENSION: INCH.
- 419B-01 OBSOLETE, NEW STANDARD 419B-02.

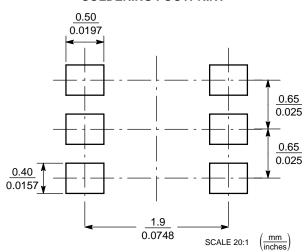
	MILLIMETERS		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3		0.20 RE	F	0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
С	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65 BSC		0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

### STYLE 6:

- PIN 1. ANODE 2 2
  - N/C
  - CATHODE 1 4. ANODE 1

  - 5. N/C 6. CATHODE 2

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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